LINEAR INTEGRATED CIRCUITS



HIGH-VOLTAGE, HIGH-CURRENT 8 DARLINGTON ARRAYS

These high-voltage, high-current Darlington transistor arrays comprise eight NPN Darlington on a common monolithic substrate. All units feature open collector outputs and integral suppression diodes for inductive loads. Peak currents of 500 mA can be withstood. They are pinned with inputs opposite outputs to facilitate circuit board layout.

- The L601 is a general-purpose array wich may be used with DTL, TTL, PMOS, CMOS, etc.
- The L602 is specifically designed for use with 14 to 25V PMOS devices. Each input has a Zener diode and resistor in series in order to limit the input current to a safe value.
- The L603 has a series base resistor to each Darlington pair, and thus allows operation directly with TTL or CMOS operating at a supply voltage of 5V.
- The L604 has a series base resistor to each Darlington pair, and thus allows operation directly with PMOS or CMOS utilizing supply voltage of 6 to 15V.

In all cases, the individual Darlington collector current rating is 400 mA. However, outputs may be paralleled for higher load current capability. The devices are supplied in a 18-lead dual in-line plastic package with copper frame.

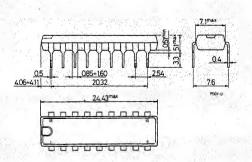
ABSOLUTE MAXIMUM RATINGS

V _{CEX}	Collector emitter voltage (input open)	90	٧
Ic	Collector current	0.4	Α
l _c	Collector peak current	0.5	Α
V.	Input voltage (for L602, L603 and L604)	30	V
I _i	Input current (for L601 only)	25	mΑ
P _{tot}	Total power dissipation a T _{amb} = 25°C	1.8	W
Top	Operating junction temperature	-25 to 150	°C
T _{stg}	Storage temperature	-55 to 150	°C
sig			

ORDERING NUMBERS: L601B, L602B, L603B, L604B

MECHANICAL DATA

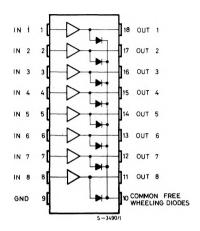
Dimensions in mm





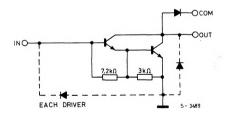
CONNECTION DIAGRAM

(top view)

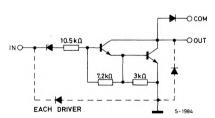


SCHEMATIC DIAGRAMS

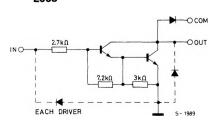
L601



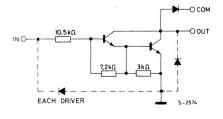
L602



L603



L604





THERMAL DATA

_				0.0.00
R _{th j-amb}	Thermal resistance junction-ambient	max	70	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb}= 25°C, unless otherwise specified)

	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CEX}	Output leakage current	V _{CE} = 90V			10	μА
V _{CE(sat)}	Collector emitter saturation voltage	I _C = 300 mA I _B = 500 μA I _C = 200 mA I _B = 350 μA I _C = 100 mA I _B = 250 μA			2 1.7 1.2	>>>
h _{FE}	DC forward current gain (L601 only)	V _{CE} = 3V I _C = 300 mA	1000			-
Vi	Minimum input voltage (ON condition)	V _{CE} = 3V I _C = 300 mA for L602 for L603 for L604			11.5 2.5 2.5	<<<
Vi	Maximum input voltage (OFF condition)	V _{CE} = 90V I _C = 25 μA for L601 for L602 for L603 for L604	0.55 7 0.75 1			>>>>
I _R	Clamp diode reverse current	V _R = 90V			50	μΑ
V _F	Clamp diode forward voltage	I _F = 300 mA		2	2.4	V
t _{on}	Turn-on delay	0.5 V _i to 0.5 V _o		0.4		μς
toff	Turn-off delay	0.5 V _i to 0.5 V _o		0.4		μs